

MOSFETs Silicon N-channel MOS (U-MOSVII-H)

# XPH4R10ANB

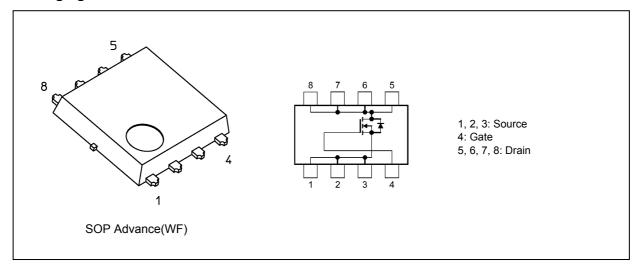
### 1. Applications

- · Automotive
- · Motor Drivers
- · Switching Voltage Regulators

#### 2. Features

- (1) AEC-Q101 qualified
- (2) Small, thin package
- (3) Low drain-source on-resistance:  $R_{DS(ON)} = 3.4 \text{ m}\Omega$  (typ.) ( $V_{GS} = 10 \text{ V}$ )
- (4) Low leakage current:  $I_{DSS}$  = 10  $\mu A$  (max) ( $V_{DS}$  = 100 V)
- (5) Enhancement mode:  $V_{th}$  = 2.5 to 3.5 V ( $V_{DS}$  = 10 V,  $I_{D}$  = 1.0 mA)

### 3. Packaging and Internal Circuit





### 4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

Characteris	Symbol	Rating	Unit		
Drain-source voltage			V <sub>DSS</sub>	100	V
Gate-source voltage			V <sub>GSS</sub>	±20	
Drain current (DC)		(Note 1)	I <sub>D</sub>	70	Α
Drain current (pulsed)		(Note 1)	I <sub>DP</sub>	210	
Power dissipation	(T <sub>c</sub> = 25 °C)		P <sub>D</sub>	170	W
Power dissipation	(t = 10 s)	(Note 2)	] [	3.0	
Power dissipation	(t = 10 s)	(Note 3)	]	0.96	
Single-pulse avalanche energy		(Note 4)	E <sub>AS</sub>	241	mJ
Single-pulse avalanche current			I <sub>AS</sub>	70	Α
Channel temperature		(Note 5)	T <sub>ch</sub>	175	°C
Storage temperature		(Note 5)	T <sub>stg</sub>	-55 to 175	

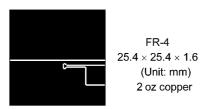
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

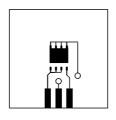
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit		
Channel-to-case thermal impedance	(T <sub>c</sub> = 25 °C)		Z <sub>th(ch-c)</sub>	0.88	°C/W
Channel-to-ambient thermal impedance	(t = 10 s)	(Note 2)	Z <sub>th(ch-a)</sub>	50	
Channel-to-ambient thermal impedance	(t = 10 s)	(Note 3)	Z <sub>th(ch-a)</sub>	156	

- Note 1: Ensure that the channel temperature does not exceed 175 °C.
- Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1
- Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2
- Note 4:  $V_{DD}$  = 80 V,  $T_{ch}$  = 25 °C (initial), L = 37.9  $\mu$ H,  $R_{G}$  = 25  $\Omega$ ,  $I_{AS}$  = 70 A
- Note 5: The definitions of the absolute maximum channel and storage temperatures are qualified per AEC-Q101.





FR-4  $25.4 \times 25.4 \times 1.6$  (Unit: mm) 2 oz copper

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



#### 6. Electrical Characteristics

# 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±1	μΑ
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V			10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	100			٧
	V <sub>(BR)DSX</sub>	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	80	_		
Gate threshold voltage	$V_{th}$	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.0 mA	2.5		3.5	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 6 V, I <sub>D</sub> = 35 A	_	4.1	6.2	mΩ
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 35 A	_	3.4	4.1	

### 6.2. Dynamic Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 300 kHz	_	4970	_	pF
Reverse transfer capacitance	C <sub>rss</sub>		_	300	_	
Output capacitance	C <sub>oss</sub>		_	1940	_	
Gate resistance	r <sub>g</sub>		_	2.1	4.2	Ω
Switching time (rise time)	t <sub>r</sub>	See Fig. 6.2.1	_	21	_	ns
Switching time (turn-on time)	t <sub>on</sub>		_	52	_	
Switching time (fall time)	t <sub>f</sub>		_	22	_	
Switching time (turn-off time)	t <sub>off</sub>		_	89	_	ns

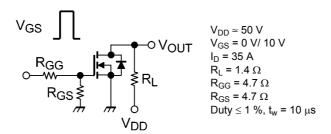


Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	$Q_g$	$V_{DD} \approx 80 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 70 \text{ A}$		75	1	nC
Gate-source charge 1	Q <sub>gs1</sub>		_	22		
Gate-drain charge	$Q_{gd}$		_	16	_	

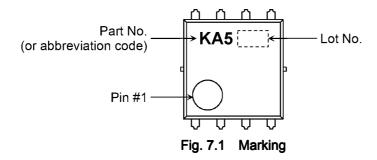
### 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (Not	e 6) I <sub>DRP</sub>	_	_	_	210	Α
Diode forward voltage	V <sub>DSF</sub>	I <sub>DR</sub> = 70 A, V <sub>GS</sub> = 0 V	_	_	-1.2	V

Note 6: Ensure that the channel temperature does not exceed 175 °C.



### 7. Marking





### 8. Characteristics Curves (Note)

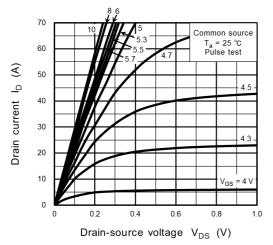


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>

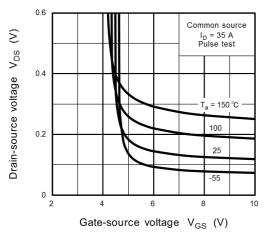


Fig. 8.3 V<sub>DS</sub> - V<sub>GS</sub>

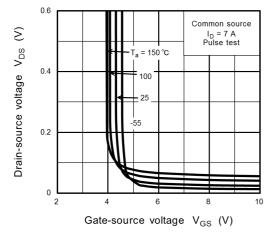


Fig. 8.5 V<sub>DS</sub> - V<sub>GS</sub>

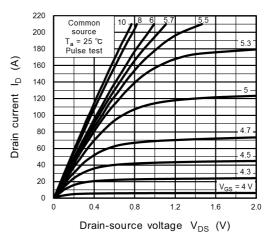
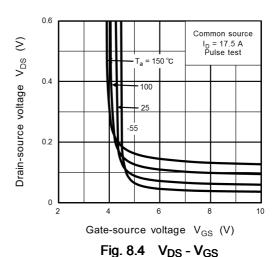


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>



0.6

Gate-source voltage  $V_{GS}$  (V) Fig. 8.6  $V_{DS}$  -  $V_{GS}$ 



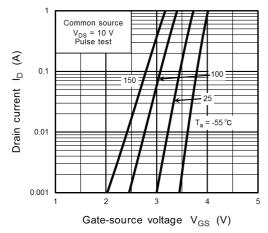


Fig. 8.7 I<sub>D</sub> - V<sub>GS</sub>

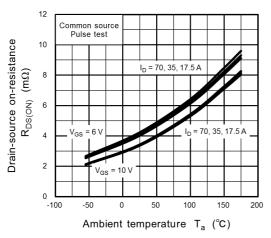


Fig. 8.9 R<sub>DS(ON)</sub> - T<sub>a</sub>

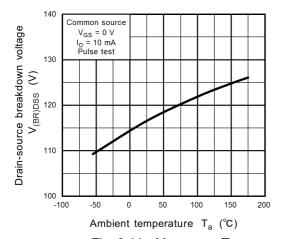


Fig. 8.11 V<sub>(BR)DSS</sub> - T<sub>a</sub>

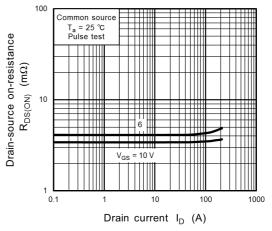


Fig. 8.8 R<sub>DS(ON)</sub> - I<sub>D</sub>

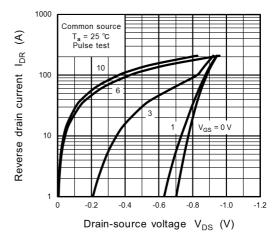


Fig. 8.10 I<sub>DR</sub> - V<sub>DS</sub>

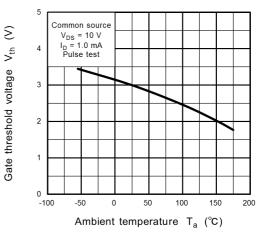


Fig. 8.12 V<sub>th</sub> - T<sub>a</sub>



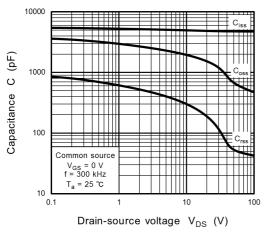


Fig. 8.13 Capacitance - V<sub>DS</sub>

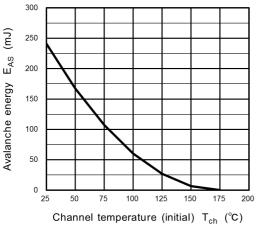


Fig. 8.15 E<sub>AS</sub> - T<sub>ch</sub>(Guaranteed Maximum)

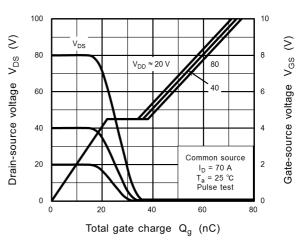


Fig. 8.14 Dynamic Input/Output Characteristics

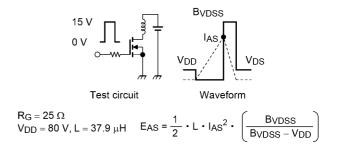


Fig. 8.16 Test Circuit/Waveform



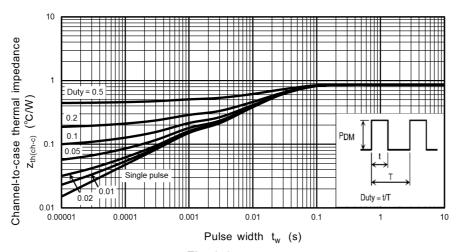
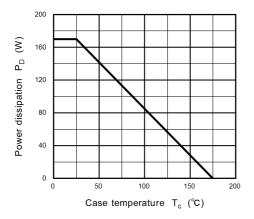


Fig. 8.17  $z_{th(ch-c)}$  -  $t_w$  (Guaranteed Maximum)



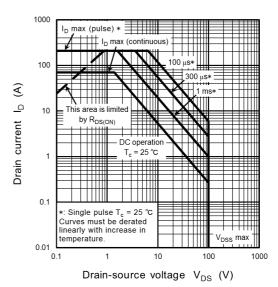


Fig. 8.18 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

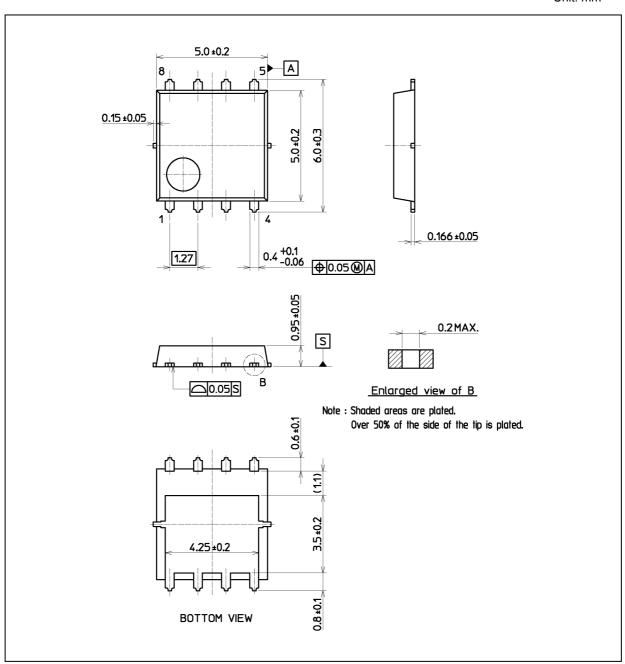
Fig. 8.19 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### **Package Dimensions**

Unit: mm



Weight: 0.083 g (typ.)

Package Name(s)
TOSHIBA: 2-5Q4A
Nickname: SOP Advance(WF)



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